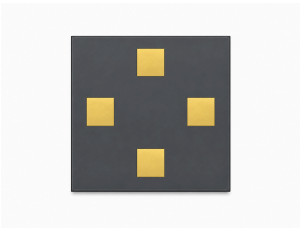
DC–40000 MHz GaAs RF crossover die

LCXOV-DC-40000-D — DC–40000 MHz GaAs RF crossover die.

Insertion loss: 0.4 dB (typical); Isolation: 30 dB (typical); Return loss: 20 dB (typical). Die dimensions: 0.6 × 0.6 × 0.1 mm.



RF characteristics

TA = +25 °C

Parameter	Symbol	Minimum	Typical	Maximum	Value	Unit
Operating frequency	-	0	-	40000	DC–40000	MHz
Insertion loss	-	-	0.4	-	-	dB
Isolation	-	-	30	-	-	dB
Return loss	-	-	20	-	-	dB

Absolute limits

Parameter	Symbol	Minimum	Typical	Maximum	Unit
Maximum input power	-	-	-	35	dBm

Environmental specifications

Parameter	Symbol	Minimum	Typical	Maximum	Unit
Storage temperature	-	-65	-	150	°C
Operating temperature	-	-55	-	125	°C

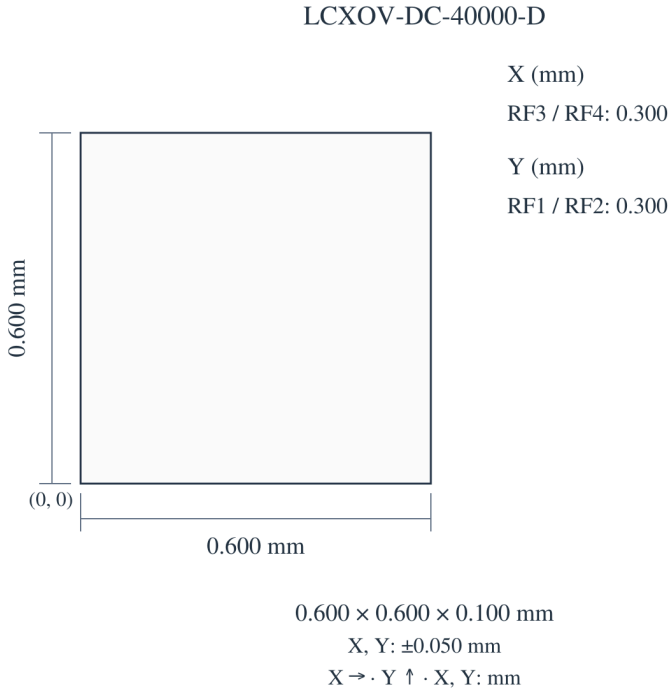
Bond-pad assignments

Pins	Symbol	Function	Notes
RF1	RF1	RF port	-
RF2	RF2	RF port	-
RF3	RF3	RF port	-
RF4	RF4	RF port	-

Die dimensions

Parameter	Value	Unit
Die dimensions	0.6 × 0.6 × 0.1	mm

Reference drawing showing selected dimensions in mm. Use complete drawings for fabrication and wire bonding.



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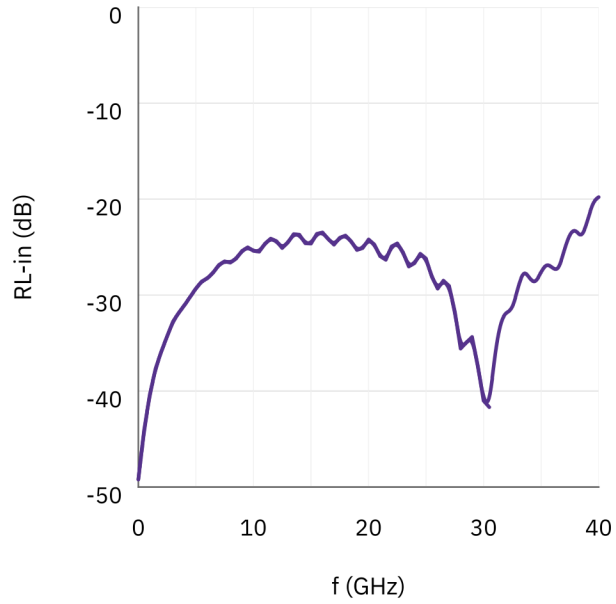
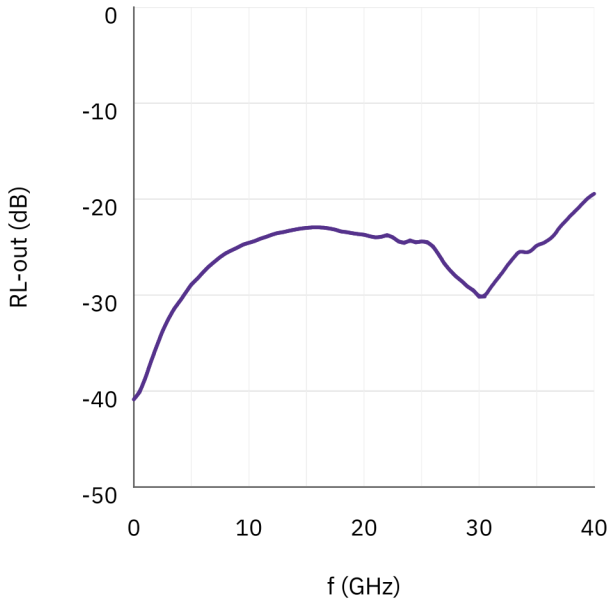
Performance curves

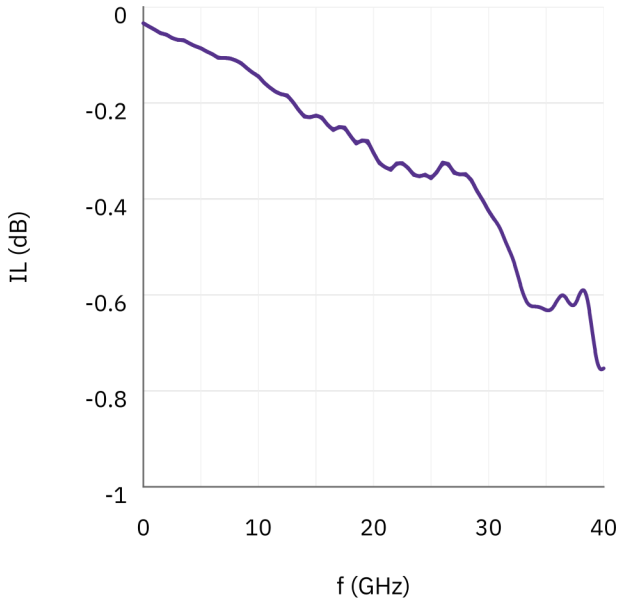
Read each figure with its stated operating conditions.

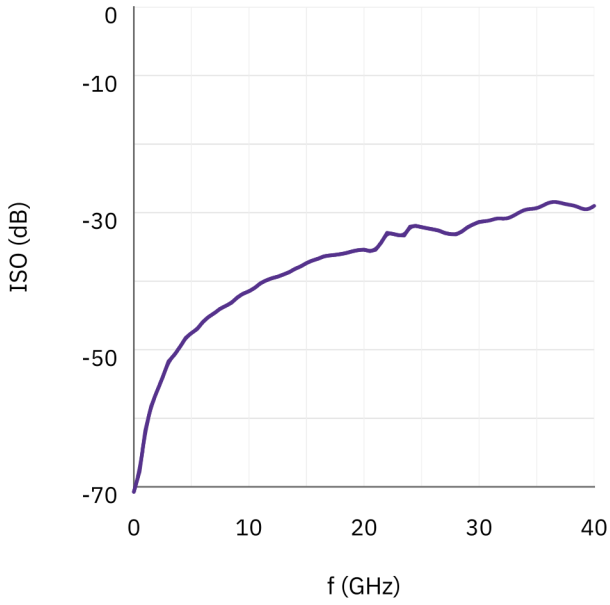
Input matching; Output matching; Insertion loss; Isolation.

Figure notes: TA=+25°C. Readings are approximate. Input return loss, output return loss and isolation are plotted as signed dB values.









Document notice

Specifications are subject to revision. Before design release, confirm the current document revision and product-specific requirements with LCRF. The approved quotation and order documentation define the supplied configuration.